



**AMPLIFIER TRANSISTOR**

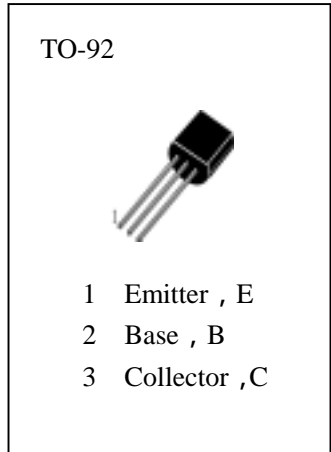
Collector-Emitter Voltage:  $V_{ce0}=160V$ .

CollectorDissipation:  $P_c(max)=625mW$

**ABSOLUTE MAXIMUM RATINGS (  $T_a=25$  )**

- $T_{stg}$ ——Storage Temperature..... -55~150
- $T_j$ ——Junction Temperature..... 150
- $P_c$ ——Collector Dissipation.....625mW
- $V_{CBO}$ ——Collector-Base Voltage.....180V
- $V_{CEO}$ ——Collector-Emitter Voltage.....160V
- $V_{EBO}$ ——Emitter-Base Voltage.....6V
- $I_c$ ——Collector Current.....600mA

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**ELECTRICAL CHARACTERISTICS (  $T_a=25$  )**

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	180			V	$I_C=100 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	160			V	$I_C=1mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	6			V	$I_E=10 \mu A, I_C=0$
ICBO	Collector Cut-off Current			50	nA	$V_{CB}=120V, I_E=0$
IEBO	Emitter-Base Cut-off Current			50	nA	$V_{EB}=4V, I_C=0$
HFE ( 1 )	DC Current Gain	80				$V_{CE}=5V, I_C=1mA$
HFE ( 2 )		80		280		$V_{CE}=5V, I_C=10mA$
HFE ( 3 )		30				$V_{CE}=5V, I_C=50mA$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			0.15	V	$I_C=10mA, I_B=-1mA$
$V_{CE(sat2)}$				0.2	V	$I_C=50mA, I_B=5mA$
$V_{BE(sat1)}$	Base-Emitter Saturation Voltage			1	V	$I_C=10mA, I_B=1mA$
$V_{BE(sat2)}$				1	V	$I_C=50mA, I_B=5mA,$
$f_T$	Current Gain-Bandwidth Product	100		300	MHZ	$V_{CE}=10V, I_C=10mA$ $F=100MHZ$